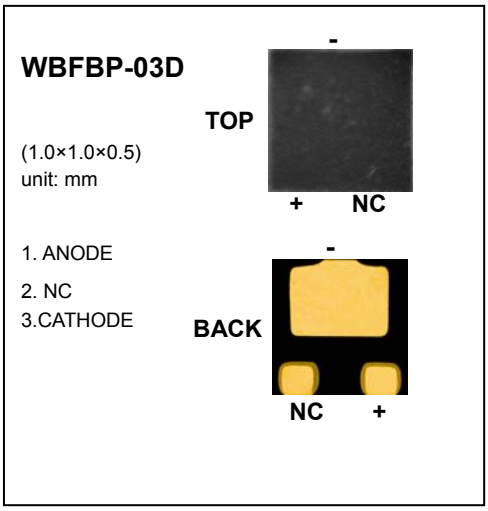
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate Diodes

DK4148LLD03 SWITCHING DIODE



DESCRIPTION

Epitaxial planar silicon diode

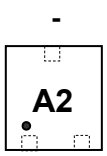
FEATURES

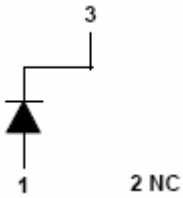
Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note Book PC, etc.)

MARKING: **A2**





Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive peak reverse voltage	V_{RM}	100	V
Peak repetitive peak reverse voltage **Working peak reverse voltage** **DC blocking voltage**	V_{RRM} V_{RWM} V_R	75	V
RMS reverse voltage	$V_{R(RMS)}$	53	V
Forward continuous current	I_{FM}	300	mA
Average rectified output current	I_O	150	mA
Peak forward surge current @t=1.0μs **@t =1.0s**	I_{FSM}	2.0 1.0	A
Power dissipation	P_D	100	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	1250	℃/W
Junction temperature	T_j	150	℃
Storage temperature	T_{STG}	-55~+150	℃

Electrical Ratings @Ta=25℃

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_{F1}			0.715	V	I_F=1mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1.0	V	I_F=50mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_{R1}			1	μA	V_R=75V
	I_{R2}			25	nA	V_R=20V
Capacitance between terminals	C_T			2	pF	V_R=0V,f=1MHz
Reverse recovery time	t_{rr}			4	ns	I_F=I_R=10mA Irr=0.1XI_R,R_L=100Ω